Supporting data

Ultra Thin Diffusion Barrier Development by Utilizing Advanced Deposition Materials in ALD

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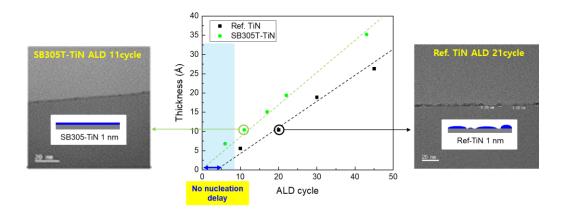


Figure 1. Thickness as a function of the number of ALD cycles.

Table 1. SEM images of TiN films before and after DHF dipping test.

Samples	Before	After
	Tilted SEM	pinhole
Ref. TiN	TiN surface	
	SIO ₂ Si ²	5-4900 10 GeV 11 3mm x40 Ge (SE(1) Grown
	Tilted SEM	
SB305T-TiN	TiN surface	
	SiO ₂ Si 2400 10 (kV 11 2mm 40) (k (56.6)	S-4800 10 GW 11 Omm ald0 D4 SE(b)

*Dip test using DHF 100:1 for 5min